

Smart Highside Power Switch

Features

- Overload protection
- Current limitation
- Short circuit protection
- Thermal shutdown
- Overvoltage protection (including load dump)
- Reverse battery protection¹⁾
- Undervoltage and overvoltage shutdown with auto-restart and hysteresis
- Open drain diagnostic output
- Open load detection in ON-state
- CMOS compatible input
- Loss of ground and loss of V_{bb} protection
- Electrostatic discharge (ESD) protection

Product Summary

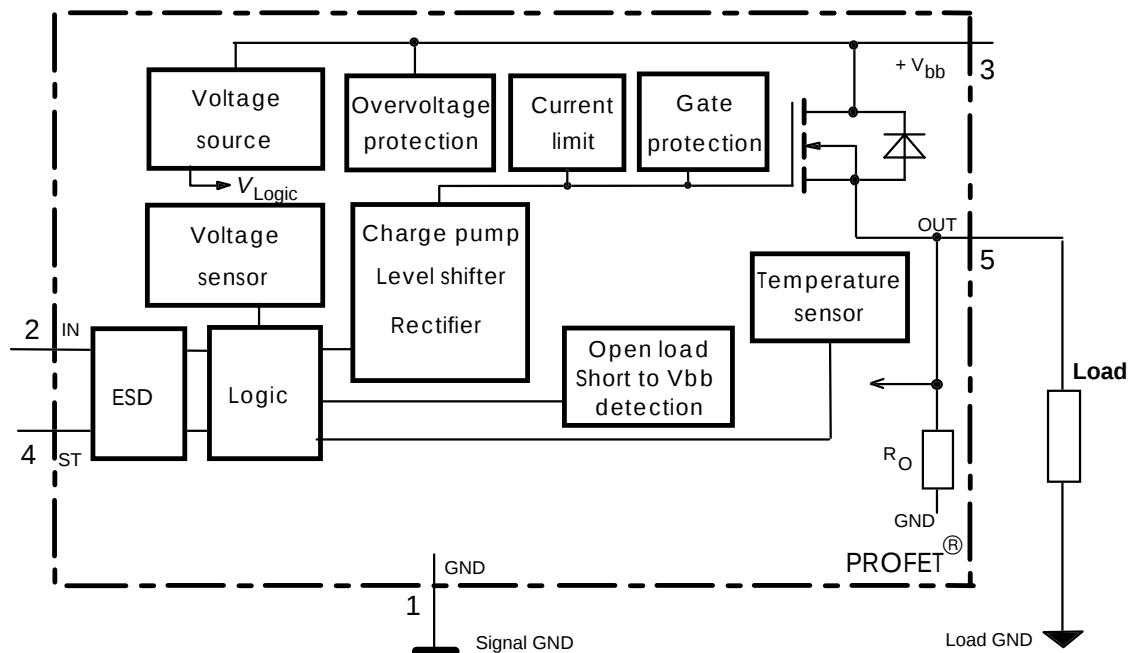
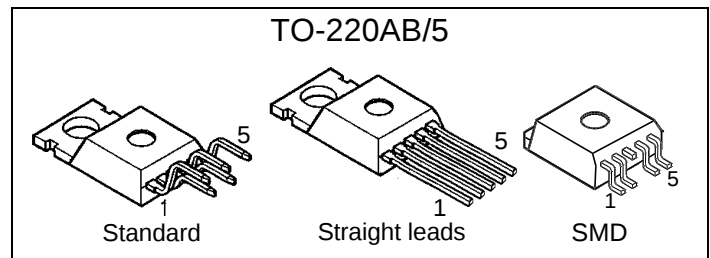
Overvoltage protection	$V_{bb(AZ)}$	43	V
Operating voltage	$V_{bb(on)}$	5.0 ... 24	V
On-state resistance	R_{ON}	60	mΩ
Load current (ISO)	$I_{L(ISO)}$	7.0	A
Current limitation	$I_{L(SCr)}$	17	A

Application

- μ C compatible power switch with diagnostic feedback for 12 V DC grounded loads
- Most suitable for resistive and lamp loads

General Description

N channel vertical power FET with charge pump, ground referenced CMOS compatible input and diagnostic feedback, monolithically integrated in Smart SIPMOS® technology. Fully protected by embedded protection functions.



¹⁾ With external current limit (e.g. resistor $R_{GND}=150\ \Omega$) in GND connection, resistor in series with ST connection, reverse load current limited by connected load.

Pin	Symbol	Function
1	GND -	Logic ground
2	IN I	Input, activates the power switch in case of logical high signal
3	V _{bb} +	Positive power supply voltage, the tab is shorted to this pin
4	ST S	Diagnostic feedback, low on failure
5	OUT (Load, L) O	Output to the load

Maximum Ratings at $T_j = 25\text{ °C}$ unless otherwise specified

Parameter	Symbol	Values	Unit
Supply voltage (overvoltage protection see page 3)	V_{bb}	43	V
Supply voltage for full short circuit protection $T_{j\text{ Start}} = -40 \dots +150\text{ °C}$	V_{bb}	24	V
Load dump protection ²⁾ $V_{\text{LoadDump}} = U_A + V_S$, $U_A = 13.5\text{ V}$ $R_l^{3)} = 2\text{ }\Omega$, $R_L = 1.7\text{ }\Omega$, $t_d = 200\text{ ms}$, IN= low or high	$V_{\text{Load dump}}^{4)}$	60	V
Load current (Short circuit current, see page 4)	I_L	self-limited	A
Operating temperature range	T_j	-40 ... +150	°C
Storage temperature range	T_{stg}	-55 ... +150	
Power dissipation (DC), $T_C \leq 25\text{ °C}$	P_{tot}	75	W
Electrostatic discharge capability (ESD) (Human Body Model) acc. MIL-STD883D, method 3015.7 and ESD assn. std. S5.1-1993	IN: V_{ESD} all other pins:	1.0 2.0	kV
Input voltage (DC)	V_{IN}	-10 ... +16	V
Current through input pin (DC)	I_{IN}	± 2.0	mA
Current through status pin (DC)	I_{ST}	± 5.0	
see internal circuit diagrams page 6			

Thermal Characteristics

Parameter and Conditions	Symbol	Values			Unit
		min	typ	max	
Thermal resistance chip - case:	R_{thJC}	--	--	1.67	K/W
junction - ambient (free air):	R_{thJA}	--	--	75	
SMD version, device on PCB ⁵⁾ :		--	34	--	

2) Supply voltages higher than $V_{bb(AZ)}$ require an external current limit for the GND and status pins, e.g. with a $150\text{ }\Omega$ resistor in the GND connection and a $15\text{ k}\Omega$ resistor in series with the status pin. A resistor for the protection of the input is integrated.

3) R_l = internal resistance of the load dump test pulse generator

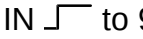
4) $V_{\text{Load dump}}$ is setup without the DUT connected to the generator per ISO 7637-1 and DIN 40839

5) Device on $50\text{ mm} \times 50\text{ mm} \times 1.5\text{ mm}$ epoxy PCB FR4 with 6 cm^2 (one layer, $70\text{ }\mu\text{m}$ thick) copper area for V_{bb} connection. PCB is vertical without blown air.

Electrical Characteristics

Parameter and Conditions at $T_j = 25^\circ\text{C}$, $V_{bb} = 12\text{ V}$ unless otherwise specified	Symbol	Values			Unit
		min	typ	max	

Load Switching Capabilities and Characteristics

On-state resistance (pin 3 to 5) $I_L = 2\text{ A}$ $T_j = 25^\circ\text{C}$: $T_j = 150^\circ\text{C}$:	R_{ON}	--	50 100	60 120	$\text{m}\Omega$
Nominal load current, ISO Norm (pin 3 to 5) $V_{ON} = 0.5\text{ V}$, $T_C = 85^\circ\text{C}$	$I_{L(ISO)}$	5.8	7.0	--	A
Output current (pin 5) while GND disconnected or GND pulled up, $V_{bb}=30\text{ V}$, $V_{IN}=0$, see diagram page 7	$I_{L(GNDhigh)}$	--	--	10	mA
Turn-on time IN  to 90% V_{OUT} :	t_{on}	80	200	400	μs
Turn-off time IN  to 10% V_{OUT} :	t_{off}	80	230	450	μs
$R_L = 12\ \Omega$, $T_j = -40\dots+150^\circ\text{C}$					
Slew rate on 10 to 30% V_{OUT} , $R_L = 12\ \Omega$, $T_j = -40\dots+150^\circ\text{C}$	dV/dt_{on}	0.1	--	1	$\text{V}/\mu\text{s}$
Slew rate off 70 to 40% V_{OUT} , $R_L = 12\ \Omega$, $T_j = -40\dots+150^\circ\text{C}$	$-dV/dt_{off}$	0.1	--	1	$\text{V}/\mu\text{s}$

Operating Parameters

Operating voltage ⁶⁾ $T_j = -40\dots+150^\circ\text{C}$:	$V_{bb(on)}$	5.0	--	24	V
Undervoltage shutdown $T_j = -40\dots+150^\circ\text{C}$:	$V_{bb(under)}$	3.5	--	5.0	V
Undervoltage restart $T_j = -40\dots+150^\circ\text{C}$:	$V_{bb(u\ rst)}$	--	--	5.0	V
Undervoltage restart of charge pump see diagram page 10 $T_j = -40\dots+150^\circ\text{C}$:	$V_{bb(ucp)}$	--	5.6	7.0	V
Undervoltage hysteresis $\Delta V_{bb(under)} = V_{bb(u\ rst)} - V_{bb(under)}$	$\Delta V_{bb(under)}$	--	0.2	--	V
Overvoltage shutdown $T_j = -40\dots+150^\circ\text{C}$:	$V_{bb(over)}$	24	--	34	V
Overvoltage restart $T_j = -40\dots+150^\circ\text{C}$:	$V_{bb(o\ rst)}$	23	--	--	V
Overvoltage hysteresis $T_j = -40\dots+150^\circ\text{C}$:	$\Delta V_{bb(over)}$	--	0.5	--	V
Overvoltage protection ⁷⁾ $I_{bb}=40\text{ mA}$ $T_j = -40\dots+150^\circ\text{C}$:	$V_{bb(AZ)}$	42	47	--	V
Standby current (pin 3) $V_{IN}=0$ $T_j = -40\dots+25^\circ\text{C}$: $T_j = 150^\circ\text{C}$:	$I_{bb(off)}$	--	10 12	25 28	μA
Leakage output current (included in $I_{bb(off)}$) $V_{IN}=0$	$I_{L(off)}$	--	--	12	μA
Operating current (Pin 1) ⁸⁾ , $V_{IN}=5\text{ V}$, $T_j = -40\dots+150^\circ\text{C}$	I_{GND}	--	1.8	3.5	mA

⁶⁾ At supply voltage increase up to $V_{bb} = 5.6\text{ V}$ typ without charge pump, $V_{OUT} \approx V_{bb} - 2\text{ V}$

⁷⁾ See also $V_{ON(CL)}$ in table of protection functions and circuit diagram page 7.

⁸⁾ Add I_{ST} , if $I_{ST} > 0$, add I_{IN} , if $V_{IN} > 5.5\text{ V}$

Parameter and Conditions at $T_j = 25\text{ °C}$, $V_{bb} = 12\text{ V}$ unless otherwise specified	Symbol	Values			Unit
		min	typ	max	

Protection Functions

Initial peak short circuit current limit (pin 3 to 5) $T_j = -40\text{ °C}$: $T_j = 25\text{ °C}$: $T_j = +150\text{ °C}$:	$I_{L(SCp)}$	27 20 12	37 30 18	47 40 25	A
Repetitive short circuit shutdown current limit $T_j = T_{jt}$ (see timing diagrams, page 9)	$I_{L(SCr)}$	--	17	--	A
Thermal overload trip temperature	T_{jt}	150	--	--	°C
Thermal hysteresis	ΔT_{jt}	--	10	--	K
Reverse battery (pin 3 to 1) ⁹⁾	$-V_{bb}$	--	--	32	V
Reverse battery voltage drop ($V_{out} > V_{bb}$) $I_L = -2\text{ A}$ $T_j = 150\text{ °C}$:	$-V_{ON(rev)}$	--	610	--	mV

Diagnostic Characteristics

Open load detection current (on-condition,) $T_j = -40\text{ °C}$: $T_j = 25\text{..}150\text{ °C}$:	$I_{L(OL)}$	150 150	600 450	950 750	mA
Open load detection voltage ¹⁰⁾ (off-condition) $T_j = -40\text{..}150\text{ °C}$:	$V_{OUT(OL)}$	2	3	4	V
Internal output pull down (pin 5 to 1), $V_{OUT} = 5\text{ V}$, $T_j = -40\text{..}150\text{ °C}$	R_O	4	10	30	kΩ

⁹⁾ Requires 150 Ω resistor in GND connection. The reverse load current through the intrinsic drain-source diode has to be limited by the connected load. Note that the power dissipation is higher compared to normal operating conditions due to the voltage drop across the intrinsic drain-source diode. The temperature protection is not active during reverse current operation! Input and Status currents have to be limited (see max. ratings page 2 and circuit page 7).

¹⁰⁾ External pull up resistor required for open load detection in off state.

Parameter and Conditions at $T_j = 25^\circ\text{C}$, $V_{bb} = 12\text{ V}$ unless otherwise specified	Symbol	Values			Unit
		min	typ	max	

Input and Status Feedback¹¹⁾

Input resistance $T_j = -40..+150^\circ\text{C}$, see circuit page 6	R_I	2.5	3.5	6	$\text{k}\Omega$
Input turn-on threshold voltage  $T_j = -40..+150^\circ\text{C}$:	$V_{IN(T+)}$	1.7	--	3.5	V
Input turn-off threshold voltage  $T_j = -40..+150^\circ\text{C}$:	$V_{IN(T-)}$	1.5	--	--	V
Input threshold hysteresis	$\Delta V_{IN(T)}$	--	0.5	--	V
Off state input current (pin 2), $V_{IN} = 0.4\text{ V}$, $T_j = -40..+150^\circ\text{C}$	$I_{IN(off)}$	1	--	50	μA
On state input current (pin 2), $V_{IN} = 3.5\text{ V}$, $T_j = -40..+150^\circ\text{C}$	$I_{IN(on)}$	20	50	90	μA
Delay time for status with open load after switch off (see timing diagrams, page 10), $T_j = -40..+150^\circ\text{C}$	$t_{d(ST\ OL4)}$	100	520	1000	μs
Status invalid after positive input slope (open load) $T_j = -40 \dots +150^\circ\text{C}$:	$t_{d(ST)}$	--	250	600	μs
Status output (open drain) Zener limit voltage $T_j = -40...+150^\circ\text{C}$, $I_{ST} = +1.6\text{ mA}$: ST low voltage $T_j = -40...+25^\circ\text{C}$, $I_{ST} = +1.6\text{ mA}$: $T_j = +150^\circ\text{C}$, $I_{ST} = +1.6\text{ mA}$:	$V_{ST(high)}$ $V_{ST(low)}$	5.4 -- --	6.1 -- --	-- 0.4 0.6	V

¹¹⁾ If a ground resistor R_{GND} is used, add the voltage drop across this resistor.

Truth Table

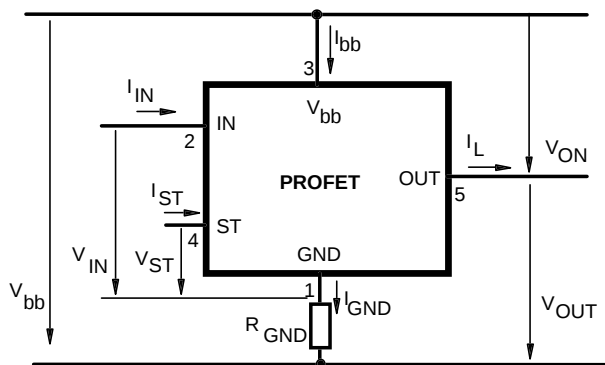
	Input-level	Output level	Status 425L1 426L1
Normal operation	L H	L H	H H
Open load	L H	¹²⁾ H	H (L ¹³⁾) L
Short circuit to V_{bb}	L H	H H	L ¹⁴⁾ H (L ¹⁵⁾)
Overtemperature	L H	L L	H L
Under-voltage	L H	L L	H H
Overvoltage	L H	L L	H H

L = "Low" Level
H = "High" Level

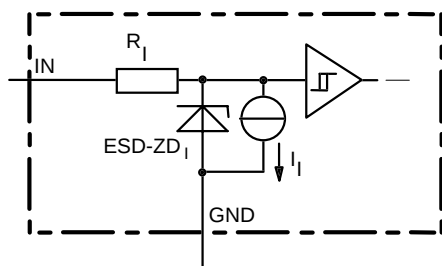
X = don't care

Z = high impedance, potential depends on external circuit
Status signal after the time delay shown in the diagrams (see fig 5. page 10)

Terms

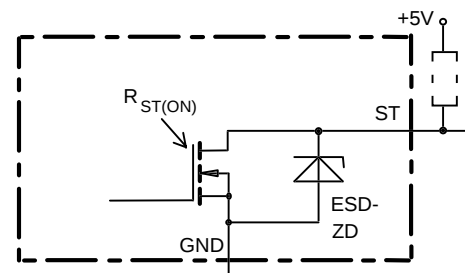


Input circuit (ESD protection)



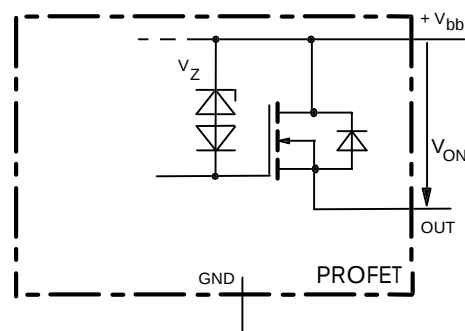
ESD zener diodes are not to be used as voltage clamp at DC conditions. Operation in this mode may result in a drift of the zener voltage (increase of up to 1 V).

Status output



ESD-Zener diode: 6.1 V typ., max 5 mA;
 $R_{ST(ON)} < 380 \Omega$ at 1.6 mA, ESD zener diodes are not to be used as voltage clamp at DC conditions. Operation in this mode may result in a drift of the zener voltage (increase of up to 1 V).

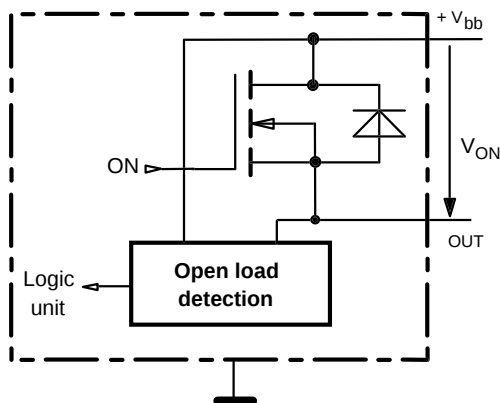
overvoltage output clamp



V_{ON} clamped to 47 V typ.

- 12) Power Transistor off, high impedance
- 13) with external resistor between pin 3 and pin 5
- 14) An external short of output to V_{bb} , in the off state, causes an internal current from output to ground. If R_{GND} is used, an offset voltage at the GND and ST pins will occur and the $V_{ST \text{ low}}$ signal may be errorious.
- 15) Low resistance to V_{bb} may be detected in ON-state by the no-load-detection

ON-state diagnostic condition: $V_{ON} < R_{ON} * I_{L(OL)}$; IN high

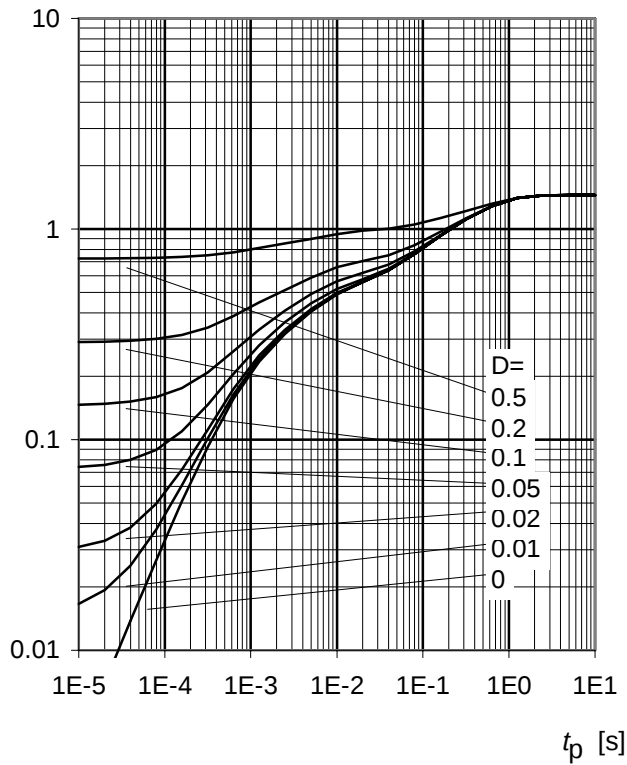


Due to $V_{GND} > 0$, no $V_{ST} = \text{low}$ signal available.

Typ. transient thermal impedance chip case

$$Z_{thJC} = f(t_p)$$

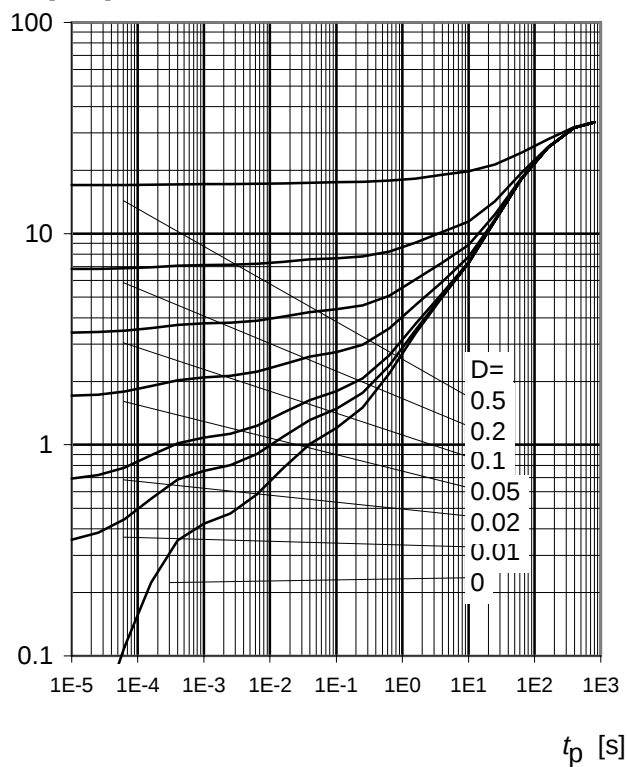
Z_{thJC} [K/W]



Typ. trans. thermal impedance chip to ambient air

$Z_{thJA} = f(t_p)$, Device on 50mm * 50mm * 1.5mm epoxy PCB FR4 with 6cm² (one layer, 70μm thick) copper area for V_{bb} connection. PCB is vertical without blown air.

Z_{thJA} [K/W]



Timing diagrams

Figure 1a: V_{bb} turn on:

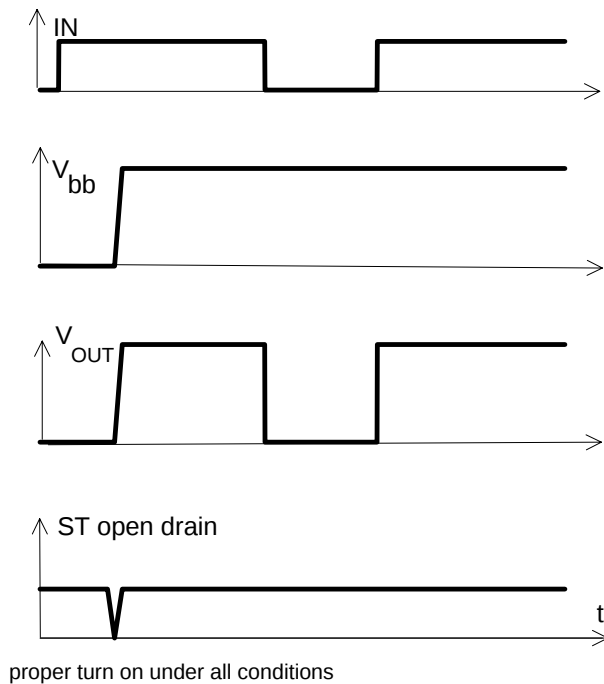


Figure 2a: Switching a lamp,

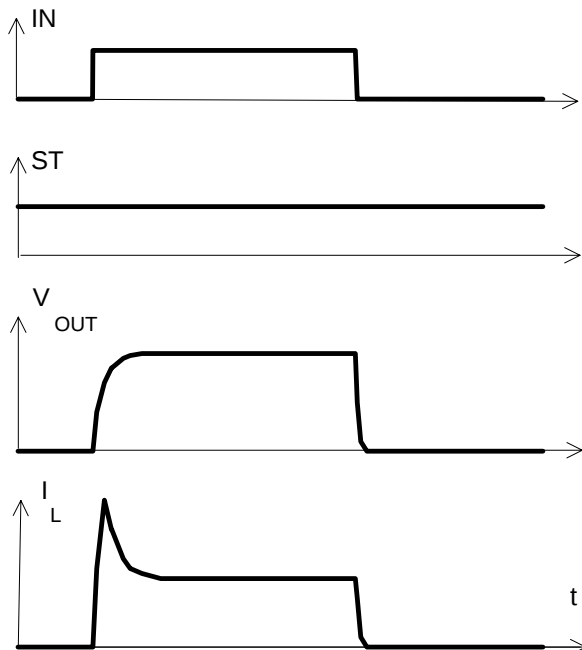


Figure 3a: Short circuit
shut down by overtemperature, reset by cooling

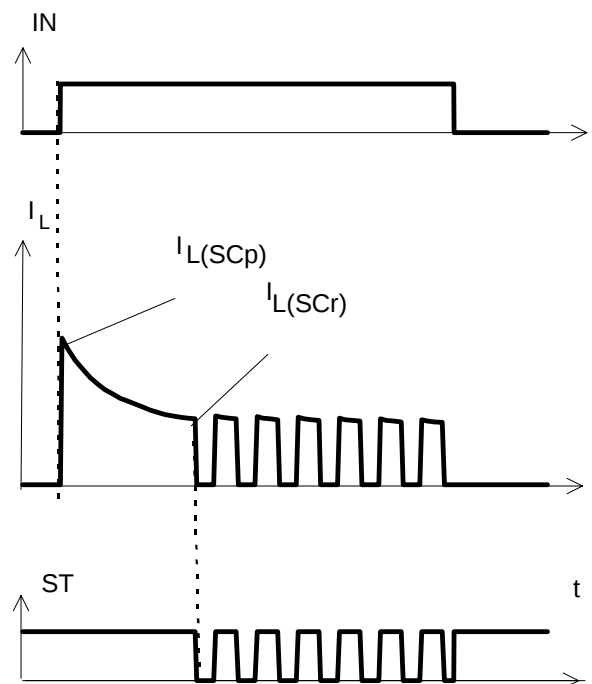


Figure 4a: Overtemperature:
Reset if $T_j < T_{jt}$

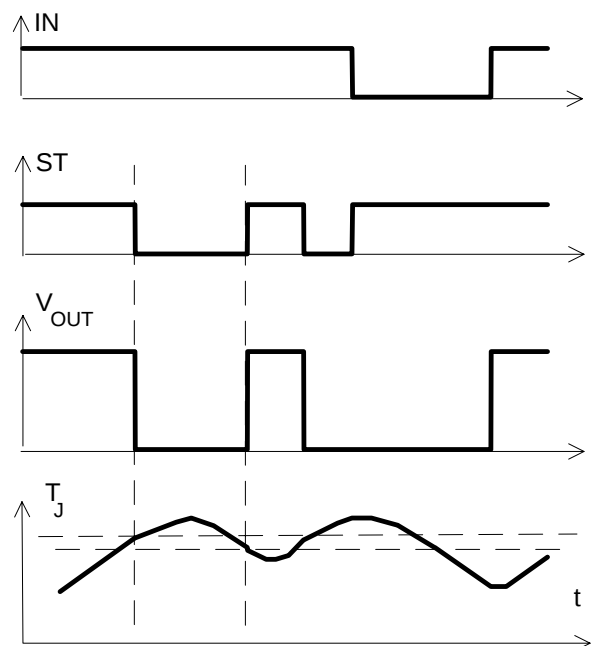
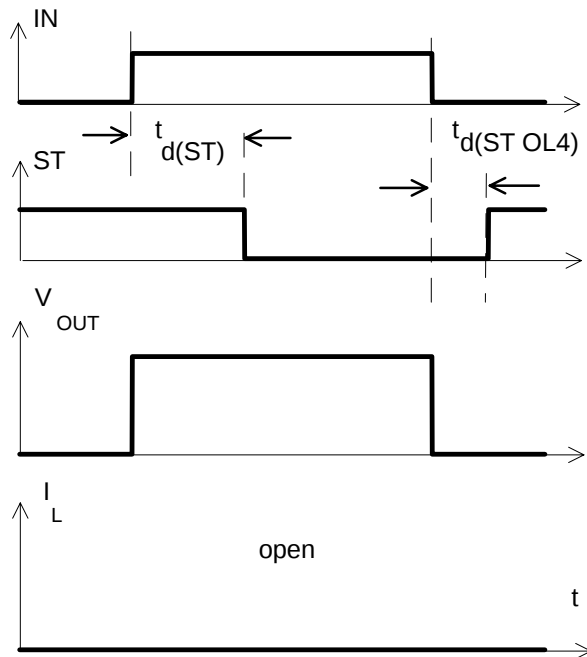


Figure 5a: Open load: detection in ON-state, turn on/off to open load



The status delay time $t_d(ST OL4)$ allows to distinguish between the failure modes "open load" and "overtemperature".

Figure 5b: Open load: detection in ON-state, open load occurs in on-state

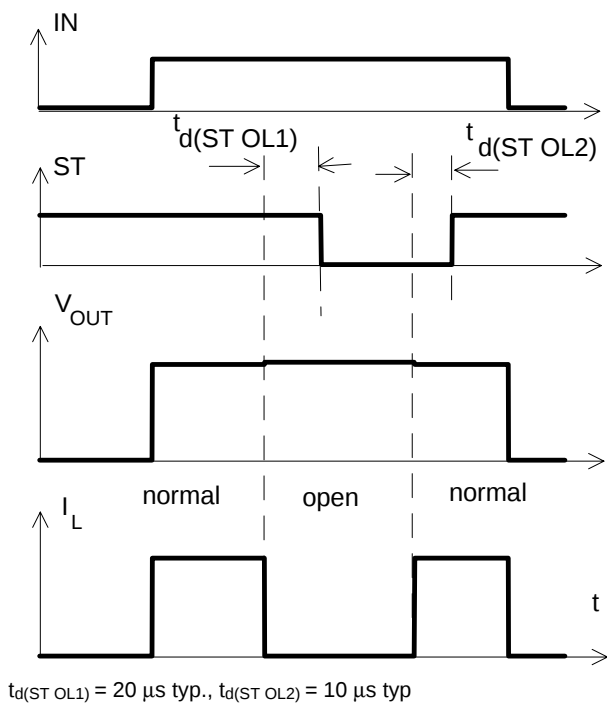


Figure 5c: Open load: detection in ON- and OFF-state (with R_{EXT}), turn on/off to open load

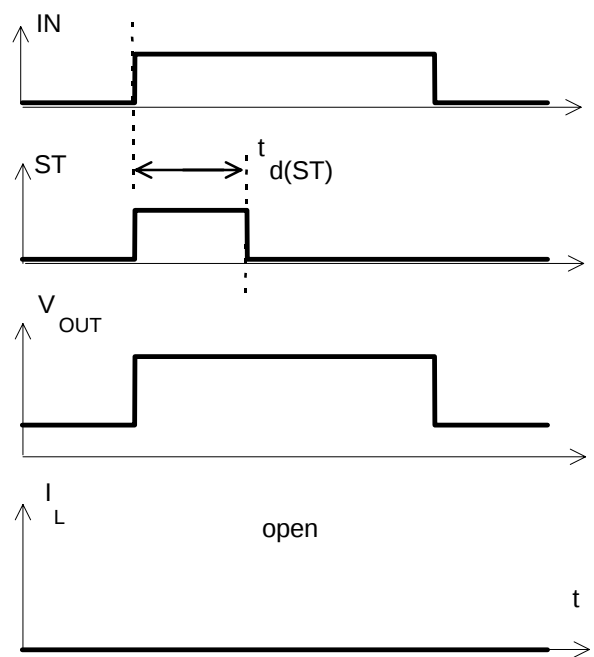


Figure 6a: Undervoltage:

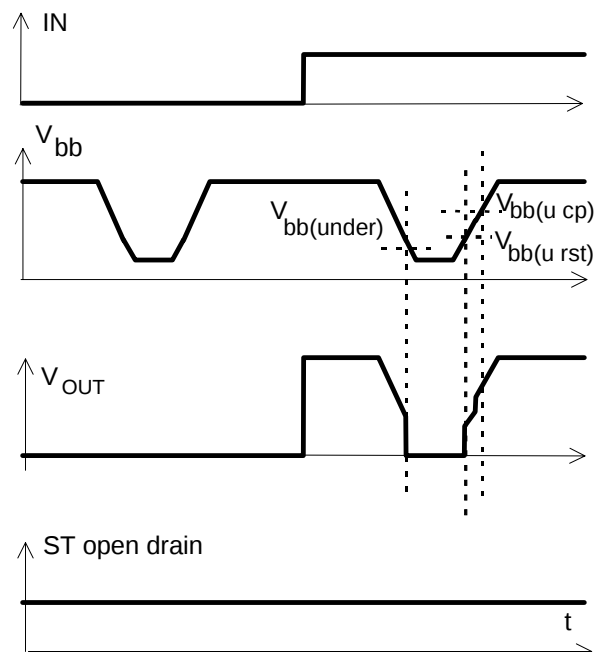


Figure 6b: Undervoltage restart of charge pump

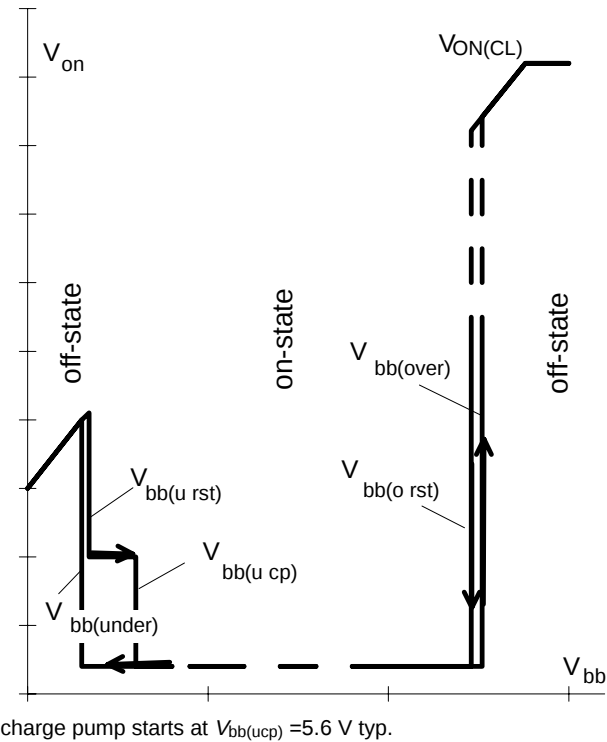
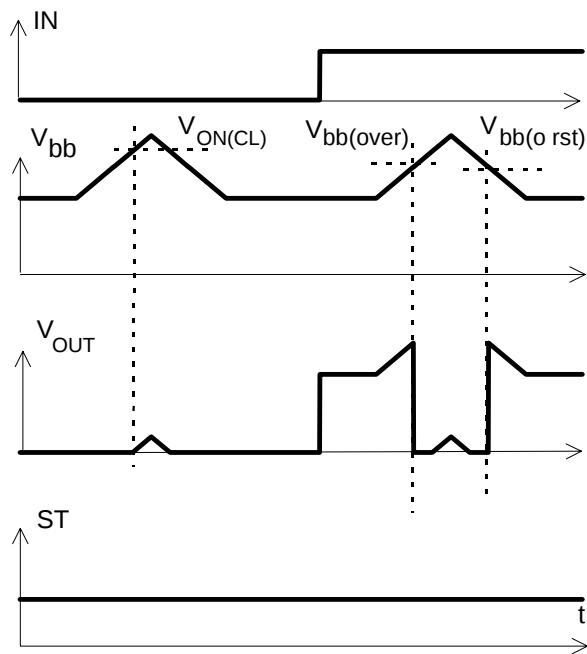


Figure 7a: Overvoltage:



Package and Ordering Code

All dimensions in mm

Standard TO-220AB/5

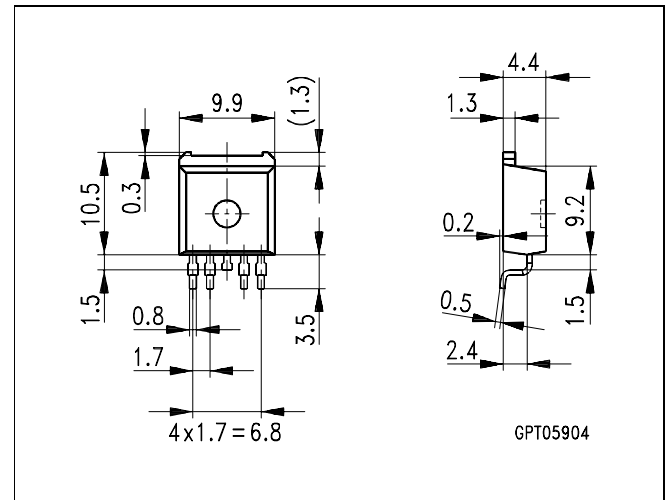
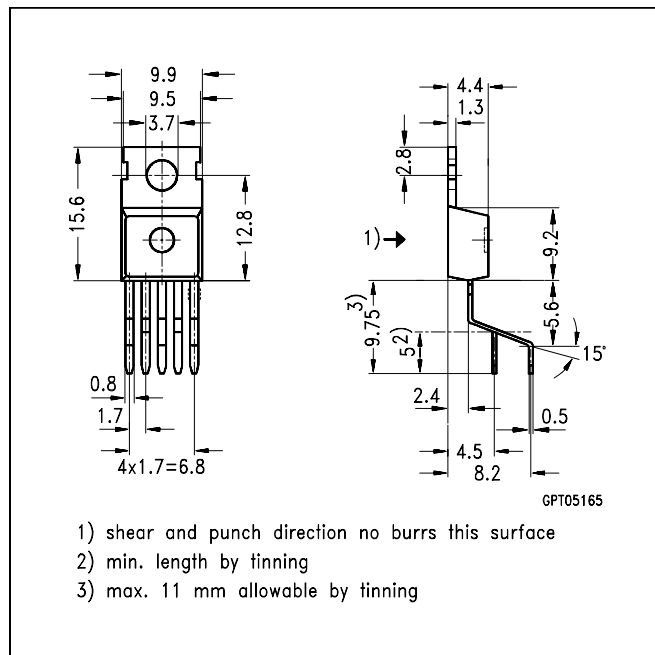
Ordering code

BTS425L1	Q67060-S6100-A2
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SMD TO-220AB/5, Opt. E3062

Ordering code

BTS425L1 E3062A	T&R: Q67060-S6100-A3
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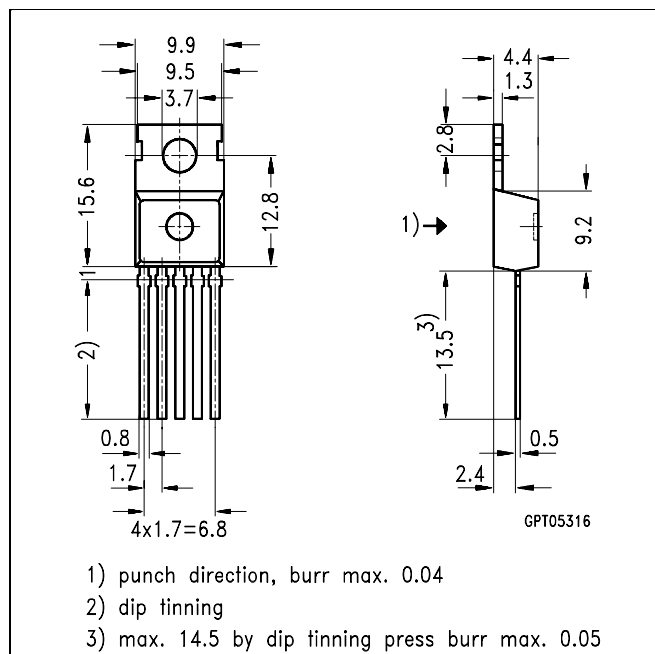


Components used in life-support devices or systems must be expressly authorised for such purpose! Critical components¹⁶⁾ of the Semiconductor Group of Siemens AG, may only be used in life supporting devices or systems¹⁷⁾ with the express written approval of the Semiconductor Group of Siemens AG.

TO-220AB/5, Option E3043

Ordering code

BTS425L1 E3043	Q67060-S6100-A4
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- 16) A critical component is a component used in a life-support device or system whose failure can reasonably be expected to cause the failure of that life-support device or system, or to affect its safety or effectiveness of that device or system.
- 17) Life support devices or systems are intended (a) to be implanted in the human body or (b) support and/or maintain and sustain and/or protect human life. If they fail, it is reasonably to assume that the health of the user or other persons may be endangered.

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